

Description

The AZ9313-01F Transient Voltage Suppressor is designed to replace multilayer varistors (MLVs) in portable applications such as cell phones, notebook computers, and PDA's. They feature large cross-sectional area junctions for conducting high transient currents, offer desirable electrical characteristics for board level protection, such as fast response time, lower operating voltage, lower clamping voltage and no device degradation when compared to MLVs. The AZ9313-01F protects sensitive semiconductor components from damage or upset due to electrostatic discharge (ESD) and other voltage induced transient events.



DFN1610-2L (Bottom View)

Feature

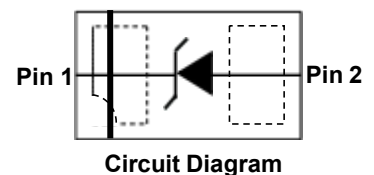
- 1500W Peak pulse power per line ($t_P = 8/20\mu s$)
- DFN1610-2L package
- Response time is typically $< 1\text{ ns}$
- Protect one I/O or power line
- Low clamping Voltage
- RoHS compliant
- Transient protection for data lines to IEC 61000-4-2(ESD) $\pm 30\text{KV}(\text{air}), \pm 30\text{KV}(\text{contact});$ IEC 61000-4-4 (EFT) 40A (5/50ns) IEC 61000-4-5 (Lightning) 150A (8/20us)

Applications

- Cell phone handsets and accessories
- Personal digital assistants (PDA's)
- Notebooks, desktops, and servers
- Portable instrumentation
- Cordless phones
- Digital cameras
- Peripherals
- MP4 players

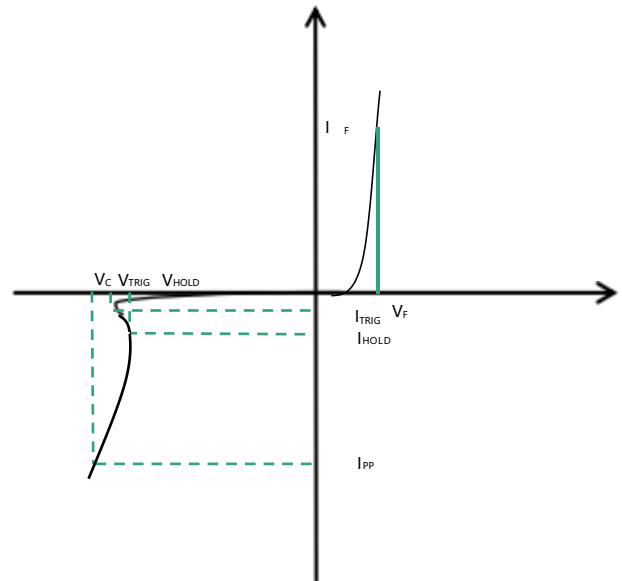
Mechanical Characteristics

- Lead finish: 100% matte Sn (Tin)
- Mounting position: Any
- Qualified max reflow temperature: 260°C
- Pure tin plating: $7 \sim 17\ \mu\text{m}$
- Pin flatness : $\leq 3\text{mil}$



Electrical Parameter

Symbol	Parameter
V_{RWM}	Peak Reverse Working Voltage
I_R	Reverse Leakage Current @ V_{RWM}
V_{TRIG}	Reverse trigger Current
V_{HOLD}	Reverse holding voltage
I_T	Test Current
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
P_{PP}	Peak Pulse Power
C_J	Junction Capacitance
I_F	Forward Current
V_F	Forward Voltage @ I_F



Electrical characteristics per line@25C(unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Peak Reverse Working Voltage	V_{RWM}				3.3	V
Reverse Breakdown voltage	V_{BR}	$I_T=1mA$	3.5			V
Reverse Current	I_R	$V_{RWM}=3.3V$			2.0	pA
Clamping Voltage	V_C	$I_{PP}=50A$ $t_P = 8/20ps$	5	7	9	V
Clamping Voltage	V_C	$I_{PP}=150A$ $t_P = 8/20ps$	9	11	13	V
Junction Capacitance	C_J	$V_R=0V$ $f = 1MHz$		40 0		pF

Absolute maximum rating@25C

Rating	Symbol	Value	Unit
Peak Pulse Power ($t_P = 8/20ps$)	P_{pp}	1500	W
Peak Pulse Current ($t_P = 8/20ps$)	I_{pp}	150	A
Lead Soldering Temperature	T_L	260 (10 sec)	°C
Operating Temperature	T_J	-55 to 150	°C
Storage Temperature	T_{STG}	-55 to 150	°C

Typical Characteristics

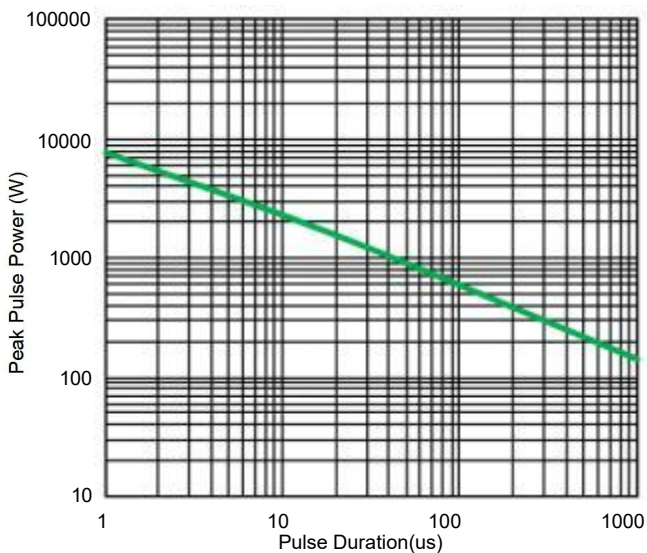
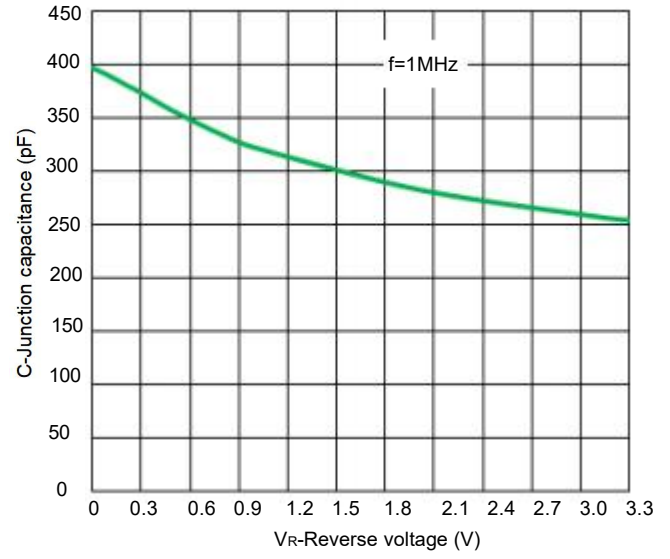
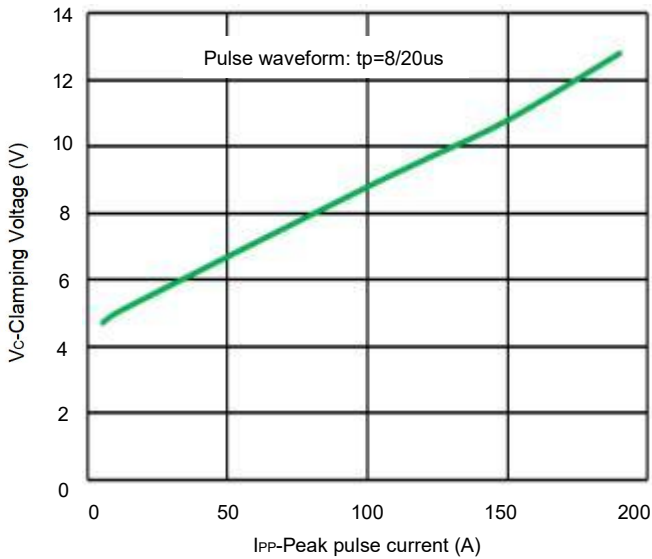
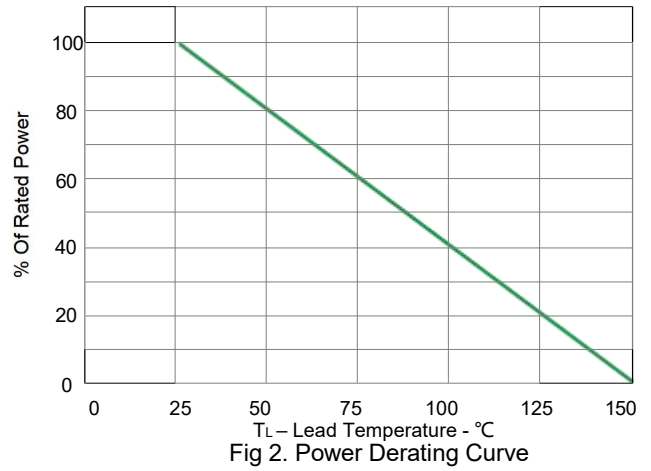
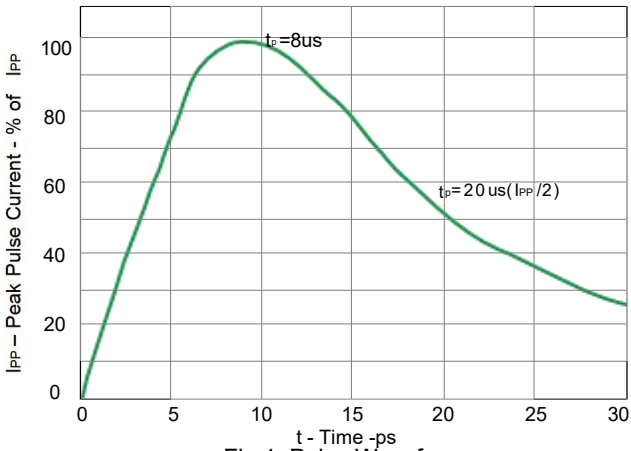
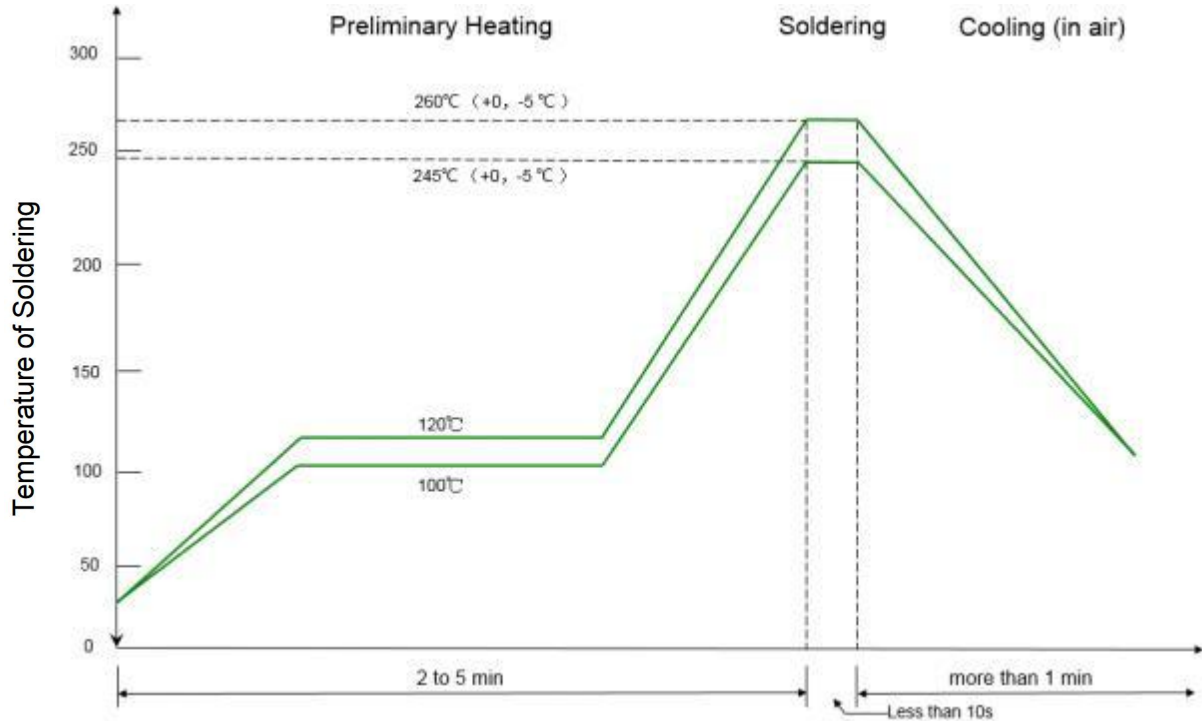


Fig 5. Non Repetitive Peak Pulse Power vs. Pulse time

Solder Reflow Recommendation



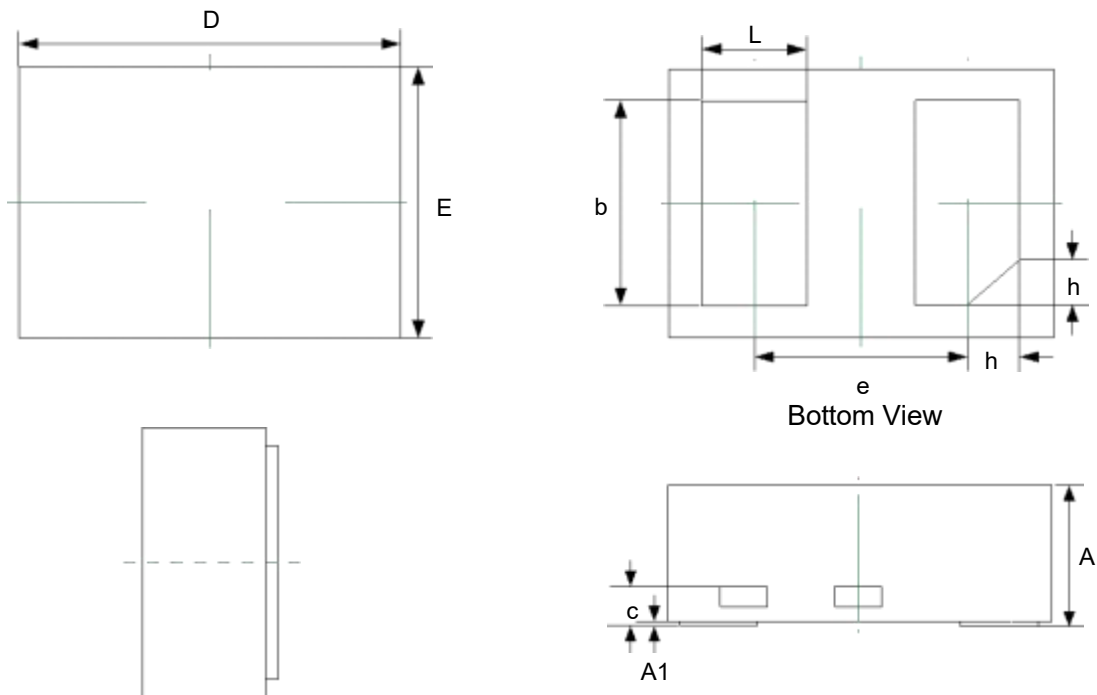
Remark: Pb free for 260°C; Pb for 245°C .

PCB Design

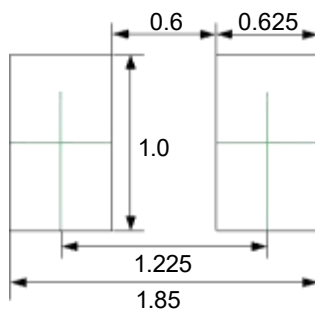
For TVS diodes a low-ohmic and low-inductive path to chassis earth is absolutely mandatory in order to achieve good ESD protection. Novices in the area of ESD protection should take following suggestions to heart:

- Do not use stubs, but place the cathode of the TVS diode directly on the signal trace.
- Do not make false economies and save copper for the ground connection.
- Place via holes to ground as close as possible to the anode of the TVS diode.
- Use as many via holes as possible for the ground connection.
- Keep the length of via holes in mind! The longer the more inductance they will have.

Product dimension (DFN1610-2L)



Dim	Millimeters	
	MIN	MAX
A	0.45	0.60
A1	--	0.05
b	0.75	0.85
c	0.10	0.20
D	1.55	1.65
e	1.10BSC	
E	0.95	1.05
L	0.35	0.45
h	0.15	0.25



Recommended Soldering Pad

Unit: mm

Ordering information

Device	Package	Reel	MPQ
TAPING	DFN1610-2L (Pb-Free)	7"	3000 / Tape & Reel